

PROCESS CP176

Power Transistor

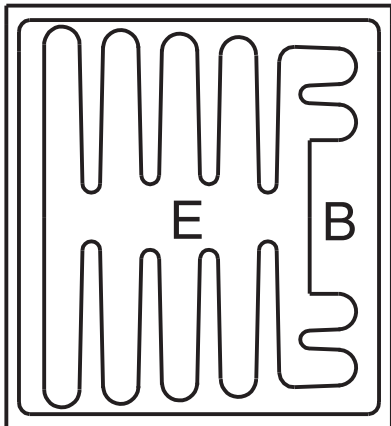
[查询"CP176"供应商](#) NPN Amps Switch Transistor Chip

CentralTM
Semiconductor Corp.

PROCESS DETAILS

Process	MULTI EPITAXIAL PLANAR
Die Size	203 x 227 MILS
Die Thickness	12.5 ± 1.0 MILS
Base Bonding Pad Area	38 x 76 MILS
Emitter Bonding Pad Area	47 x 72 MILS
Top Side Metalization	Al - 50,000Å
Back Side Metalization	Ag - 10,000Å

GEOMETRY



BACKSIDE COLLECTOR ^{R0}

GROSS DIE PER 4 INCH WAFER

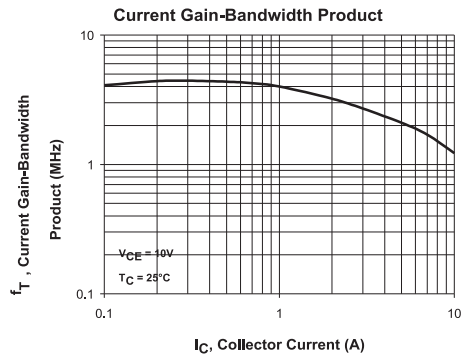
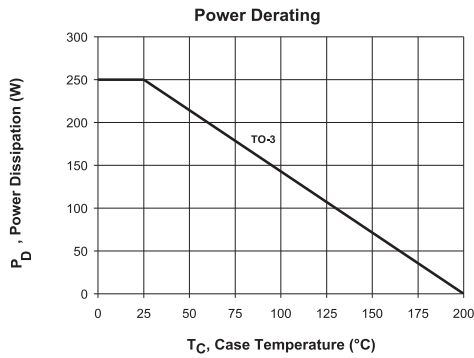
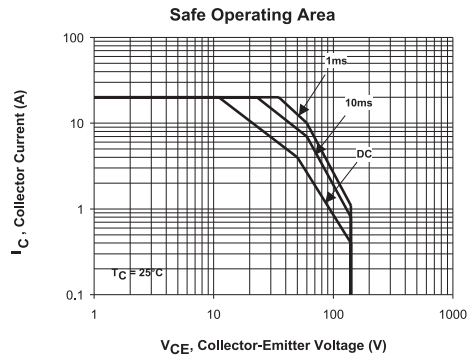
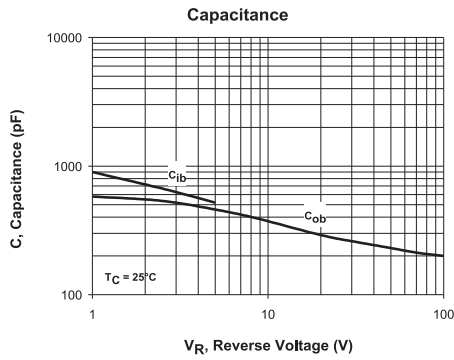
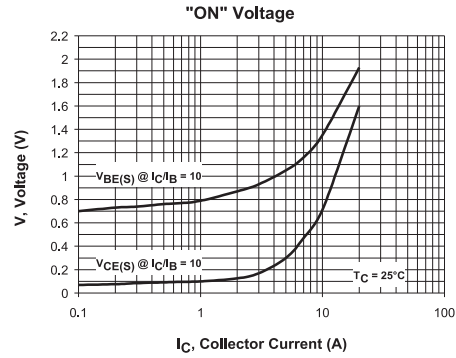
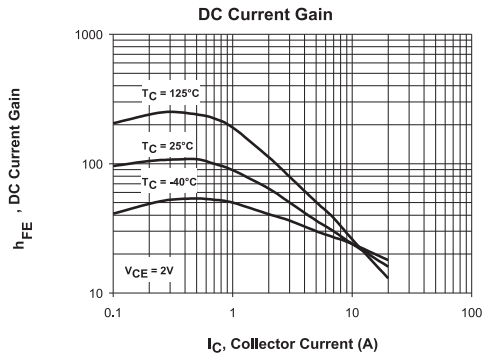
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PRINCIPAL DEVICE TYPES

MJ15003

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